Appl. No. : 10/557,694

Filed: November 22, 2005

## AMENDMENTS TO THE CLAIMS

1. (Currently amended) A resin for a photoresist composition, having a first structural unit that comprises a hydroxyl group bonded to a carbon atom at a polymer terminal, wherein [[a]] carbon atom in an α position to said hydroxyl group has at least one electron attractive group the first structural unit comprises a -CR<sup>1</sup>R<sup>2</sup>OH group, wherein R<sup>1</sup> and R<sup>2</sup> each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R<sup>1</sup> and R<sup>2</sup> is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups, wherein said -CR<sup>1</sup>R<sup>2</sup>OH group is located at a polymer terminal of said resin.

## (Canceled).

- 3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
- 4. (Currently amended) A resin for a photoresist composition according to claim 1 [[2]], wherein a proportion of the first structural units (M1) unit comprising said -CR<sup>1</sup>R<sup>2</sup>OH group is at least 1 mol%, relative to a combined 100 mol% of all structural units other than said first structural units (M1) unit within said resin for a photoresist composition.
- 5. (Currently amended) A resin for a photoresist composition having according to claim 1, wherein said first structural comprises a substituent with a pKa value within a range from 6 to 12 at a polymer terminal.

## 6. (Canceled)

7. **(Previously presented)** A resin for a photoresist composition according to claim 1, further comprising an acid dissociable, dissolution inhibiting group.

Appl. No. : 10/557,694

Filed: November 22, 2005

8. (Original) A resin for a photoresist composition according to claim 7, further comprising (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group, and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring.

- 9. **(Original)** A resin for a photoresist composition according to claim 8, further comprising (a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.
- 10. **(Previously presented)** A resin for a photoresist composition according to claim 1, with a weight average molecular weight of no more than 12,000.
- 11. **(Previously presented)** A photoresist composition, comprising a resin for a photoresist composition according to claim 1.
- 12. **(Original)** A photoresist composition according to claim 11, further comprising an acid generator as a component (B).
- 13. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.
- 14. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2) shown below:

$$R^{1}$$
  $SO_{2}$  ...  $(b-1)$   $R^{2}$   $SO_{2}$   $SO_{2}$  ...  $(b-1)$   $R^{3}$   $SO_{2}$  ...  $(b-1)$   $R^{2}$   $S^{+}$   $SO_{2}$  ...  $SO_{2}$ 

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wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom;  $R^1$  to  $R^3$  each represent, independently, an aryl group or an alkyl group, and at least one of  $R^1$  to  $R^3$  is an aryl group.

- 15. **(Original)** A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.
- 16. **(Original)** A photoresist composition according to claim 11, further comprising a nitrogen-containing organic compound.
- 17. **(Original)** A method for forming a resist pattern, using a photoresist composition according to claim 11.
- 18. (New) A resin for a photoresist composition according to claim 1, wherein a proportion of the first structural units constituting said resin is 1-5 mol%, relative to a combined 100 mol% of all structural units other than said first structural units within said resin.
- 19. (New) A resin for a photoresist composition according to claim 1, wherein the first structural unit which includes the carbon atom in the  $\alpha$ -position of said hydroxyl group having at least one electron attractive group is substantively bonded only to the polymer terminal.
- 20. (New) A resin for a photoresist composition according to claim 5, wherein a proportion of the first structural units which have the substituents with a pKa value between 6 and 12 constituting said resin is 1-5 mol% relative to a combined 100 mol% of all structural units other than said first structural units within said resin.
- 21. (New) A resin for a photoresist composition according to claim 5, wherein the substituents with a pKa value between 6 and 12 are substantively bonded only to the polymer terminal.